

2.5V TO 3.3V HIGH PERFORMANCE CLOCK BUFFER

FEATURES:

- High performance 1:10 clock driver for general purpose applications
- Operates up to 200MHz at VDD = 3.3V
- Pin-to-pin skew < 100ps
- VDD range: 2.3V to 3.6V
- · Output enable glitch suppression
- · Distributes one clock input to two banks of five outputs
- 25Ω on-chip series dampening resistors
- Available in TSSOP package

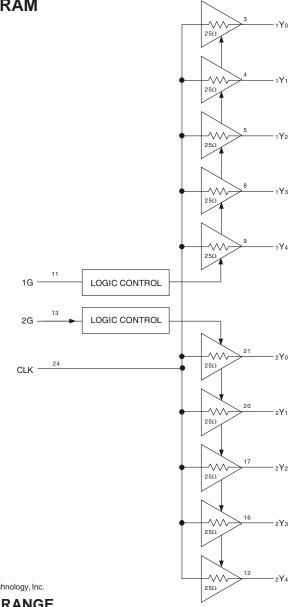
NOTE: EOL for non-green parts to occur on 5/13/10 per PDN U-09-01

FUNCTIONAL BLOCK DIAGRAM

DESCRIPTION:

The IDT5V2310 is a high performance, low skew clock buffer that operates up to 200MHz. Two banks of five outputs each provide low skew copies of CLK. Through the use of control pins 1G and 2G, the outputs of banks 1Y(0:4) and 2Y(0:4) can be placed in a low state regardless of CLK input. The device operates in 2.5V and 3.3V environments. The built-in output enable glitch suppression ensures a synchronized output enable sequence to distribute full period clock signals.

The IDT5V2310 is characterized for operation from -40°C to +85°C.

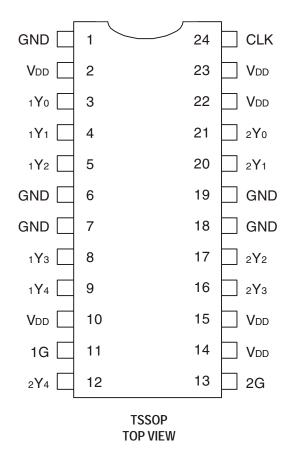


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INDUSTRIAL TEMPERATURE RANGE

DECEMBER 2012

PINCONFIGURATION



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Description	Max	Unit
Vdd	Power Supply Voltage	-0.5 to +4.6	V
VI	Input Voltage ⁽²⁾	-0.5 to VDD +0.5	V
Vo	Output Voltage ⁽²⁾	-0.5 to VDD +0.5	V
Ік	Input Clamp Current VI < 0 or VI > VDD	±50	mA
Іок	Output Clamp Current Vo < 0 or Vo > Vod	±50	mA
lo	Continuous Total Output Current Vo < 0 to VDD	±50	mA
Tstg	Storage Temperature	-65 to +150	°C

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. Not to exceed 4.6V.

CAPACITANCE(TA = +25°C, f = 1MHz, VIN = 0V)

Parameter	Description	Min.	Тур.	Max.	Unit
CIN	Input Capacitance	_	2.5		рF
	VI = 0V or VDD				

FUNCTION TABLE⁽¹⁾

	Inputs	Out	outs	
1G	2G	CLK	1 Y (0:4)	2Y(0:4)
L	L	Х	L	L
Н	L	Н	Н	L
L	Н	Н	L	Н
Н	Н	H	Н	Н

NOTE:

L = LOW Vollage Lev

^{1.} H = HIGH Voltage Level L = LOW Voltage Level

PIN DESCRIPTION

TERM	NAL	
Symbol	I/O	Description
1G	Ι	Output Enable Control for 1Y(0:4) Outputs. This output enable is active HIGH. If this pin is Logic HIGH, the 1Y(0:4) clock outputs will follow the input clock (CLK). If this pin is logic LOW, the 1Y(0:4) outputs will drive low independent of the state of CLK.
2G	Ι	Output Enable Control for 2Y(0:4) Outputs. This output enable is active HIGH. If this pin is Logic HIGH, the 2Y(0:4) clock outputs will follow the input clock (CLK). If this pin is logic LOW, the 2Y(0:4) outputs will drive low independent of the state of CLK.
1 Y (0:4)	0	Buffered Output Clocks
2 Y(0:4)	0	Buffered Output Clocks
CLK	I	Input Reference Frequency
GND		Ground
Vdd	PWR	DC Power Supply, 2.3V to 3.6V

RECOMMENDED OPERATING RANGE

Symbol	Description		Min.	Тур.	Max.	Unit
Vdd	Internal Power Supply Voltage		2.3	2.5		V
				3.3	3.6	
Vil	Input Voltage LOW	VDD = 3V to 3.6V			0.8	V
		VDD = 2.3V to 2.7V			0.7	
Vih	Input Voltage HIGH	VDD = 3V to 3.6V	2			V
		VDD = 2.3V to 2.7V	1.7			
VI	Input Voltage		0		Vdd	V
Іон	Output Current HIGH	VDD = 3V to 3.6V			-12	mA
		VDD = 2.3V to 2.7V			-6	
IOL	Output Current LOW	VDD = 3V to 3.6V			12	mA
		VDD = 2.3V to 2.7V			6	
TA	Ambient Operating Temperature	<u>;</u>	-40		+85	°C

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
Vik	InputVoltage	$V_{DD} = 3V$, $I_{IN} = -18mA$			- 1.2	V
lin	Input Current	$V_I = 0V \text{ or } V_{DD}$			±5	μA
ldd	Static Device Current ⁽¹⁾	CLK = 0V or Vdd, Io = 0mA, Vdd = 3.3V			25	μA

NOTE:

1. For IDD over frequency, see TEST CIRCUIT AND WAVEFORMS.

DC ELECTRICAL CHARACTERISTICS - $V_{DD} = 3.3V \pm 0.3V$

Symbol	Parameter	Test Cor	nditions	Min.	Тур.(1)	Max	Unit
		$V_{DD} = Min.$ to Max.	Іон = -100μА	Vdd - 0.2			
Vон	HIGH level Output Voltage	Vdd = 3V	Іон = -12mA	2.1			V
			Iон = -6mA	2.4			
		$V_{DD} = Min.$ to Max.	Ιοι = 100μΑ			0.2	
Vol	LOW level Output Voltage	$V_{DD} = 3V$	IoL = 12mA			0.8	V
			Iol = 6mA			0.55	
		$V_{DD} = 3V$	Vo = 1V	-28			
Іон	HIGH level Output Current	$V_{DD} = 3.3V$	Vo = 1.65V		-36		mA
		VDD = 3.6V	Vo = 3.135V			-14	
		Vdd = 3V	Vo = 1.95V	28			
Iol	LOW level Output Current	Vdd = 3.3V	Vo = 1.65V		36		mA
		VDD = 3.6V	Vo = 0.4V			14	

NOTE:

1. All typical values are at respective nominal $V_{\text{DD}}.$

DC ELECTRICAL CHARACTERISTICS - $V_{DD} = 2.5V \pm 0.2V$

Symbol	Parameter	Test Cor	ditions	Min.	Тур.(1)	Max	Unit
Vон	HIGH level Output Voltage	VDD = Min. to Max.	Іон = -100μА	Vdd - 0.2			V
		Vdd = 2.3V	Iон = -6mA	1.8			
Vol	LOW level Output Voltage	VDD = Min. to Max.	Ιοι = 100μΑ			0.2	V
		$V_{DD} = 2.3V$	Iol = 6mA			0.55	
		$V_{DD} = 2.3V$	Vo = 1V	-17			
Іон	HIGH level Output Current	$V_{DD} = 2.5V$	Vo = 1.25V		-25		mA
		$V_{DD} = 2.7V$	Vo = 2.375V			-10	
		$V_{DD} = 2.3V$	Vo = 1.2V	17			
IOL	LOW level Output Current	$V_{DD} = 2.5V$	Vo = 1.25V		25		mA
		Vdd = 2.7V	Vo = 0.3V			10	

NOTE:

1. All typical values are at respective nominal VDD.

TIMING REQUIREMENTS OVER RECOMMENDED RANGE

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
fcl.k	Clock Frequency	$V_{DD} = 3V$ to $3.6V$	0		200	MHz
		VDD = 2.3V to 2.7V	0		170	

SWITCHING CHARACTERISTICS OVER OPERATING RANGE-

$V_{DD} = 3.3V \pm 0.3V^{(1)}$

Symbol	Parameter	Test Conditions	Min.	Тур. ⁽¹⁾	Мах	Unit
t PLH	CLK to Yx	f = 0MHz to 200MHz	1.3		2.8	ns
t PHL						
tsк(o) ⁽²⁾	Output Skew, Yx to Yx				100	ps
tsk(p)	Pulse Skew				250	ps
tsk(pp)	Part-to-Part Skew				500	ps
tR	RiseTime	Vo = 0.4V to 2V ⁽³⁾	0.7		2	V/ns
tr	FallTime	$V_0 = 2V \text{ to } 0.4V^{(3)}$	0.7		2	V/ns
tsu	G before CLK \downarrow	V(THRESHOLD) = VDD/2	0.1			ns
tH	G after CLK↓		0.4			

NOTES:

1. All typical values are at respective nominal VDD.

2. This specification is only valid for equal loading of all outputs.

3. Measured at 100MHz.

SWITCHING CHARACTERISTICS OVER OPERATING RANGE-

$V_{DD} = 2.5V \pm 0.2V^{(1)}$

Symbol	Parameter	Test Conditions	Min.	Тур. ⁽¹⁾	Max	Unit
t PLH	CLK to Yx	f = 0MHz to 170MHz	1.5		3.5	ns
t PHL						
tsk(o) ⁽²⁾	Output Skew, Yx to Yx				100	ps
tsk(p)	Pulse Skew				400	ps
tsk(pp)	Part-to-Part Skew				600	ps
tR	RiseTime	Vo = 0.4V to 1.7V ⁽³⁾	0.5		1.4	V/ns
tr	FallTime	$V_0 = 1.7V$ to $0.4V^{(3)}$	0.5		1.4	V/ns
tsu	G before CLK↓	V(THRESHOLD) = VDD/2	0.1			ns
tH	G after CLK↓		0.4]

NOTES:

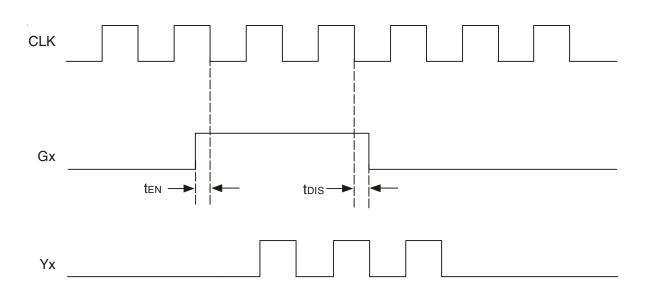
1. All typical values are at respective nominal VDD.

2. This specification is only valid for equal loading of all outputs.

3. Measured at 100MHz.

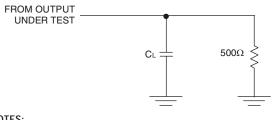
OUTPUT ENABLE GLITCH SUPPRESSION CIRCUIT

The purpose of the glitch suppression circuitry is to ensure the output enable sequence is synchronized with the clock input such that the output buffer will be enabled on the next full period of the input clock (negative edge triggered by the input clock). The G input must be stable one ten - time prior to the falling edge of the CLK for predictable operation.



G (ten, tois) Relative to CLK↓

TEST CIRCUITS AND WAVEFORMS

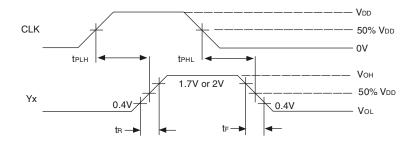


NOTES:

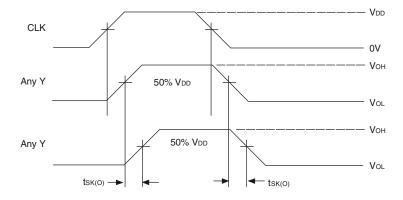
1. C_{L} includes probe and jig capacitance.

2. All input pulses are supplied by generators having the following characteristics: PRR \leq 200MHz; Zo = 50 Ω ; t_R < 1.2ns; t_F < 1.2ns.

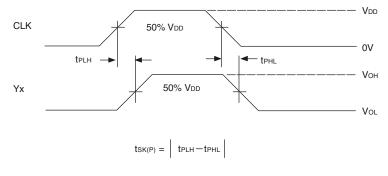
Test Load Circuit



Voltage Waveforms Propagation Delay Times

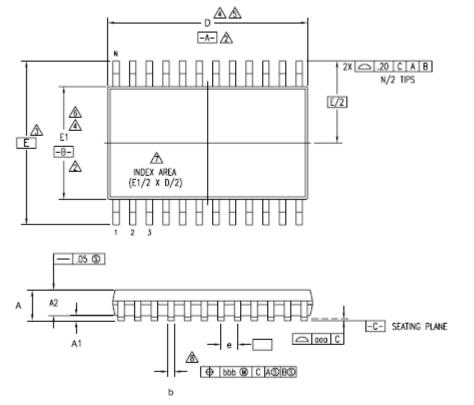


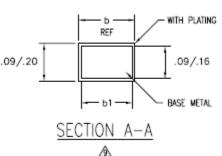
Output Skew





PACKAGE DRAWING AND DIMENSIONS (24-PIN TSSOP)





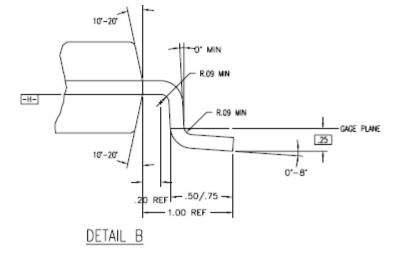
JEDE	C VARIAT	ION	N
	AD		
MIN	NOM	MAX	E
-	-	1.20	
.05	-	.15	
.80	1.00	1.05	
7.70	7.80	7.90	4,5
(6.40 BSC		3
			~
4.30	4.40	4.50	4,6
	4.40 .65 BSC		-
			-
	.65 BSC	4.50	-
.19	.65 BSC	4.50 .30	-
.19	.65 BSC	4.50 .30 .25	-

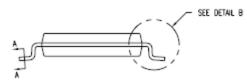
NOTES:

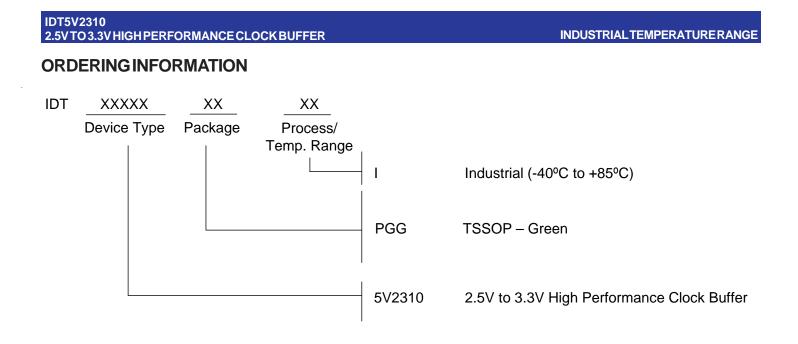
- 1 ALL DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M-1994
- ▲ DATUMS _A_ AND _B_ TO BE DETERMINED AT DATUM PLANE _H_
- ▲ DIMENSION E TO BE DETERMINED AT SEATING PLANE _____
- ▲ DIMENSIONS D AND E1 ARE TO BE DETERMINED AT DATUM PLANE -H-
- DIMENSION D DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED .15 mm PER SIDE
- DIMENSION E1 DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS. INTERLEAD FLASH OR PROTRUSIONS SHALL NOT EXCEED .25 mm PER SIDE
- DETAIL OF PIN 1 IDENTIFIER IS OPTIONAL BUT MUST BE LOCATED WITHIN THE ZONE INDICATED
- LEAD WIDTH DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS .08 mm IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT
- THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .10 AND .25 mm FROM THE LEAD TIP
- 10 ALL DIMENSIONS ARE IN MILLIMETERS
- 11 THIS OUTLINE CONFORMS TO JEDEC PUBLICATION 95 REGISTRATION MO-153, VARIATION AA, AB-1, AB, AC, AD & AE

MARKING DIAGRAM









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